MOSFETs Silicon N-channel MOS (U-MOSⅧ-H)

TK65G10N1

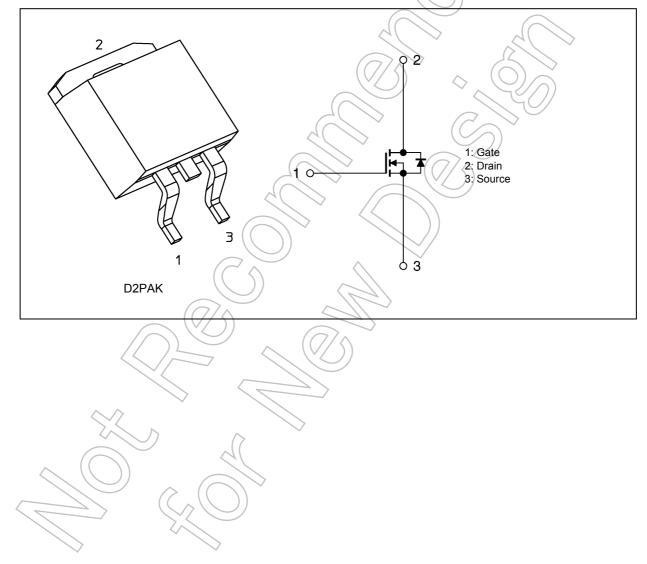
1. Applications

• Switching Voltage Regulators

2. Features

- (1) Low drain-source on-resistance: $R_{DS(ON)} = 3.8 \text{ m}\Omega \text{ (typ.)} (V_{GS} = 10 \text{ V})$
- (2) Low leakage current: $I_{DSS} = 10 \ \mu A \ (max) \ (V_{DS} = 100 \ V)$
- (3) Enhancement mode: $V_{th} = 2.0$ to 4.0 V ($V_{DS} = 10$ V, $I_D = 1.0$ mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteris	Symbol	Rating	Unit		
Drain-source voltage			V _{DSS}	100	V
Gate-source voltage			V _{GSS}	±20	
Drain current (DC)	(Silicon limit)	(Note 1, 2)	I _D	136	Α
Drain current (DC)		(Note 1, 3)	ID	65	
Drain current (pulsed)	(t = 1 ms)	(Note 1)	I _{DP}	283	
Power dissipation	(T _c = 25°C)		PD	156	W
Single-pulse avalanche energy		(Note 4)	EAS	93	mJ
Avalanche current			IAR	65	Α
Channel temperature			Tch	150	°C
Storage temperature			(T _{stg})	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

	Characteristics	$(\bigcirc/5)$	Symbol	Max	Unit
Channel-to-case thermal resistance	$\langle \langle \rangle \rangle$		R _{th(ch-c)}	0.8	°C/W

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: Limited by silicon chip capability. Package limit is 100 A.

Note 3: Device mounted with heatsink so that Rth(ch-a) becomes 2.77°C/W.

Note 4: V_{DD} = 80 V, T_{ch} = 25°C (initial), L = 17.1 μ H, I_{AR} = 65 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

6. Electrical Characteristics

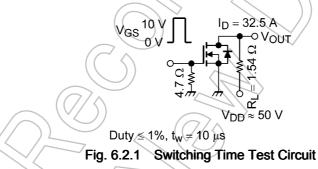
6.1. Static Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	V_{GS} = ±20 V, V_{DS} = 0 V	_	_	±0.1	μA
Drain cut-off current	I _{DSS}	V _{DS} = 100 V, V _{GS} = 0 V	\swarrow	—	10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	100		_	V
Drain-source breakdown voltage (Note 5)	V _{(BR)DSX}	I _D = 10 mA, V _{GS} = -20 V	65)2	_	
Gate threshold voltage	V _{th}	V _{DS} = 10 V, I _D = 1.0 mA	2.0	/_	4.0	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 10 V, I _D = 32.5 A	$\langle \cdot \rangle$	3.8	4.5	mΩ

Note 5: If a reverse bias is applied between gate and source, this device enters V_{(BR)DSX} mode. Note that the drainsource breakdown voltage is lowered in this mode.

6.2. Dynamic Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 50 V, V _{GS} = 0 V, f = 1 MHz	-((5400	_	pF
Reverse transfer capacitance	C _{rss}			42) —	
Output capacitance	C _{oss}		\sim	950		
Gate resistance	r _g			2.4		Ω
Switching time (rise time)	t _r	See Figure 6.2.1.]	19	_	ns
Switching time (turn-on time)	t _{on}	$(\land) \land (\land) : (: $	<u> </u>	44		
Switching time (fall time)	t _f		<u> </u>	26	_	
Switching time (turn-off time)	t _{off}		_	85	_	



6.3. Gate Charge Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

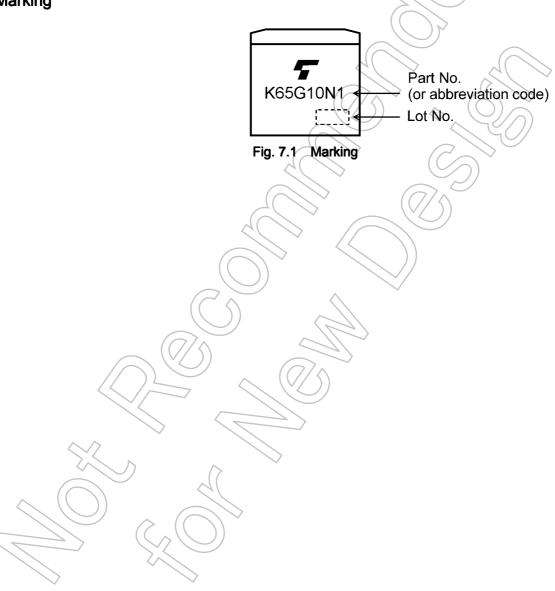
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 80$ V, V_{GS} = 10 V, I_D = 65 A	—	81	—	nC
Gate-source charge 1	Q _{gs1}		_	31	_	
Gate-drain charge	Q _{gd}		_	18	_	
Gate switch charge	Q _{SW}		_	32	_	

6.4. Source-Drain Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

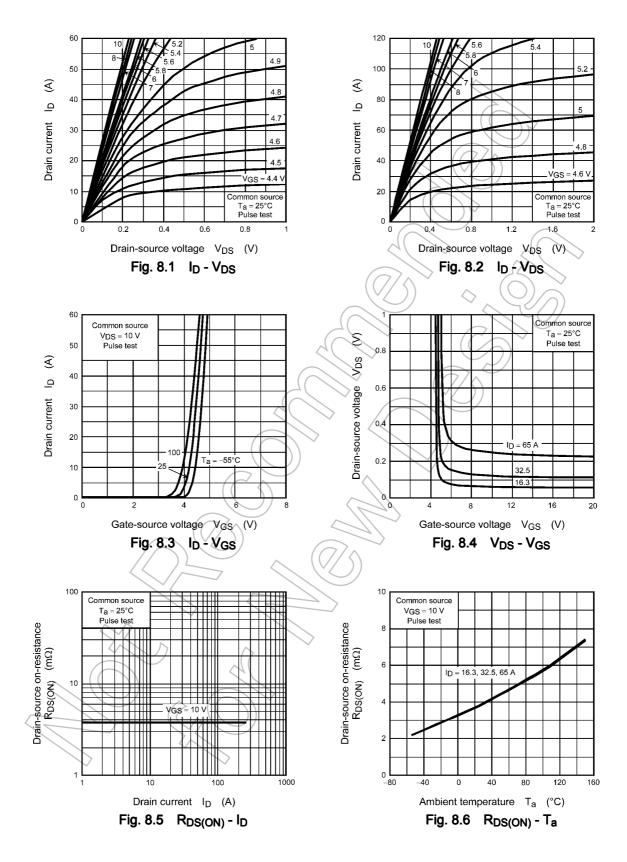
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (DC)	(Note 6)	I _{DR}	—	_	_	65	А
Reverse drain current (pulsed)	(Note 6)	I _{DRP}	—	—	—	283	
Diode forward voltage		V _{DSF}	I _{DR} = 65 A, V _{GS} = 0 V	7	—	-1.2	V
Reverse recovery time	(Note 7)	t _{rr}	I _{DR} = 65 A, V _{GS} = 0 V	\rightarrow	76		ns
Reverse recovery charge	(Note 7)	Q _{rr}	-dl _{DR} /dt = 100 A/μs	(\leftarrow)	152		nC

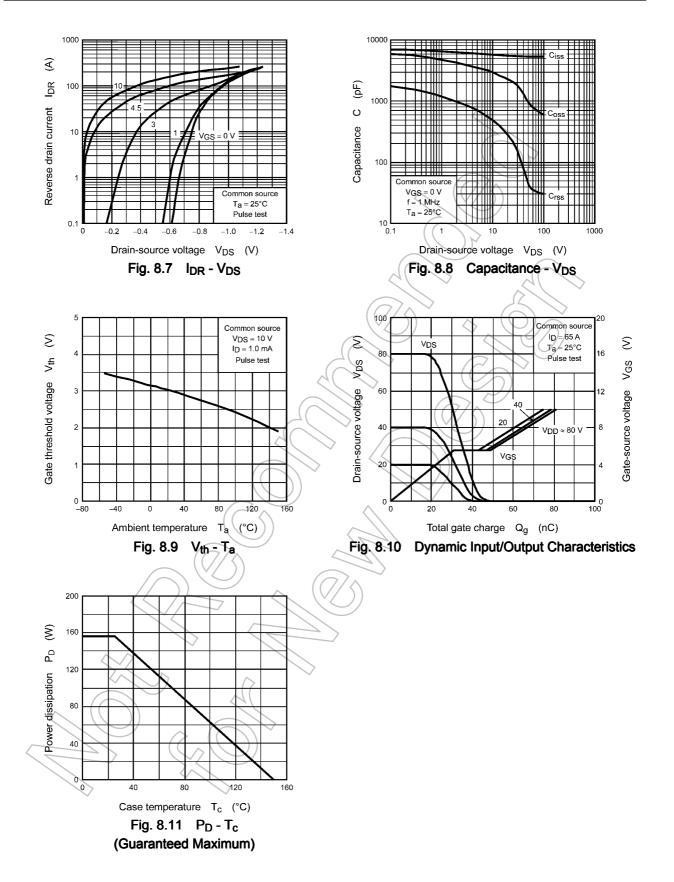
Note 6: Ensure that the channel temperature does not exceed 150°C. Note 7: Ensure that V_{DS} peak does not exceed V_{DSS} .

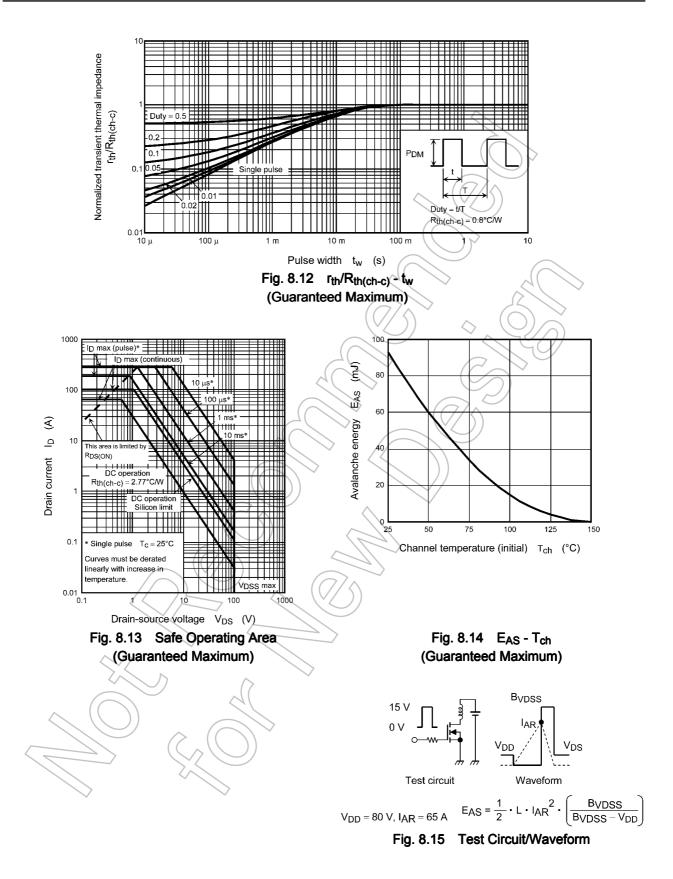
7. Marking



8. Characteristics Curves (Note)







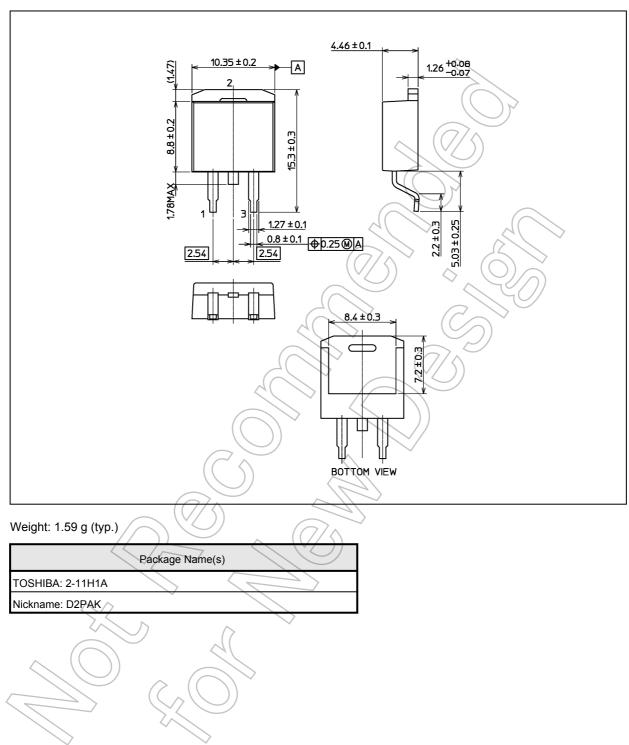
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

TK65G10N1

Unit: mm



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